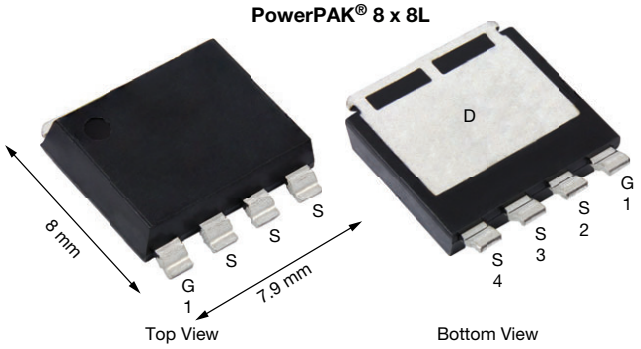
Automotive N-Channel 40 V (D-S) 175 °C MOSFET



FEATURES

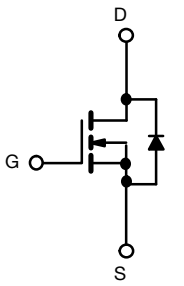
- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Thin 1.6 mm package
- Very low thermal resistance
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE GRADE

Pb-free

RoHS COMPLIANT

HALOGEN FREE



N-Channel MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	40
$R_{DS(on)}$ (Ω) at V_{GS} = 10 V	0.00124
I_D (A)	460
Configuration	Single
Package	PowerPAK 8 x 8L

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	40	V
Gate-source voltage		V_{GS}	± 20	
Continuous drain current	T_C = 25 °C	I_D	460	A
	T_C = 125 °C		265	
Continuous source current (diode conduction)		I_S	450	
Pulsed drain current [b]		I_{DM}	900	
Single pulse avalanche current	L = 0.1 mH	I_{AS}	48	
Single pulse avalanche energy		E_{AS}	115.2	mJ
Maximum power dissipation	T_C = 25 °C	P_D	500	W
	T_C = 125 °C		166	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) [d]			260	

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount [c]	R_{thJA}	44	°C/W
Junction-to-case (drain)		R_{thJC}	0.3	

Notes

a. Package limited
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %
c. When mounted on 1" square PCB (FR4 material)
d. See solder profile (www.vishay.com/doc?73257). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

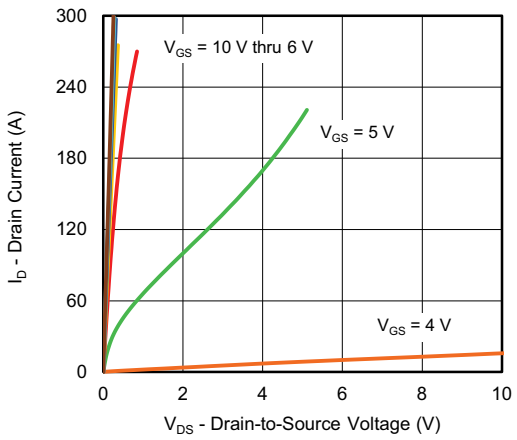
SPECIFICATIONS (T_C = 25 °C, unless otherwise noted)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static							
Drain-source breakdown voltage	V_{DS}	V_{GS} = 0, I_D = 250 µA		40	-	-	V
Gate-source threshold voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA		2	3	3.5	
Gate-source leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	V_{GS} = 0 V	V_{DS} = 40 V	-	-	1	µA
		V_{GS} = 0 V	V_{DS} = 40 V, T_J = 125 °C	-	-	200	
		V_{GS} = 0 V	V_{DS} = 40 V, T_J = 175 °C	-	-	330	
On-state drain current [a]	$I_{D(on)}$	V_{GS} = 10 V	V_{DS} ≥ 5 V	100	-	-	A
Drain-source on-state resistance [a]	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 20 A	-	0.00100	0.00124	Ω
		V_{GS} = 10 V	I_D = 20 A, T_J = 125 °C	-	-	0.00200	
		V_{GS} = 10 V	I_D = 20 A, T_J = 175 °C	-	-	0.00240	
Forward transconductance [b]	g_{fs}	V_{DS} = 15 V, I_D = 60 A		-	150	-	S
Dynamic [b]							
Input capacitance	C_{iss}	V_{GS} = 0 V	V_{DS} = 25 V, f = 1 MHz	-	5360	6975	pF
Output capacitance	C_{oss}			-	2070	2700	
Reverse transfer capacitance	C_{rss}			-	167	215	
Total gate charge [c]	Q_g	V_{GS} = 10 V	V_{DS} = 20 V, I_D = 20 A	-	92	130	nC
Gate-source charge [c]	Q_{gs}			-	26	-	
Gate-drain charge [c]	Q_{gd}			-	20.1	-	
Gate resistance	R_g	f = 1 MHz		0.65	1.59	2.56	Ω
Turn-on delay time [c]	$t_{d(on)}$	V_{DD} = 20 V, R_L = 1 Ω I_D ≅ 20 A, V_{GEN} = 10 V, R_g = 1 Ω		-	18.5	26	ns
Rise time [c]	t_r			-	18	25	
Turn-off delay time [c]	$t_{d(off)}$			-	37	52	
Fall time [c]	t_f			-	14	20	
Source-Drain Diode Ratings and Characteristics [b]							
Reverse recovery time	t_{rr}	V_{DD} = 32 V, I_{FM} = 15 A, di/dt = 100 A/µs		-	59	-	ns
Reverse recovery charge	Q_{rr}			-	69	-	nC
Reverse recovery current	I_{RM}			-	2	3.2	A
Pulsed current [a]	I_{SM}			-	-	900	A
Forward voltage	V_{SD}	I_F = 50 A, V_{GS} = 0		-	0.8	1.1	V

Notes

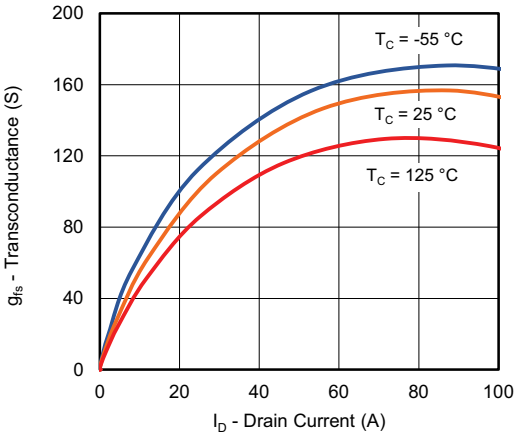
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

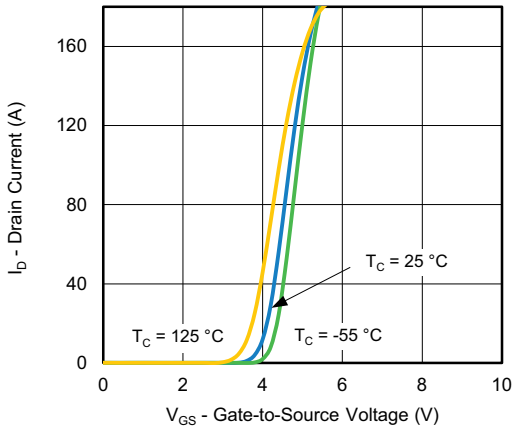
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



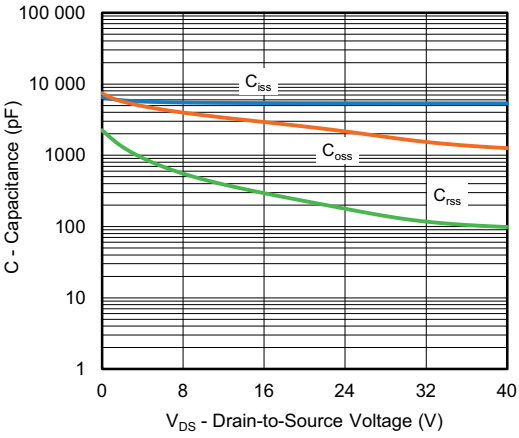
Output Characteristics



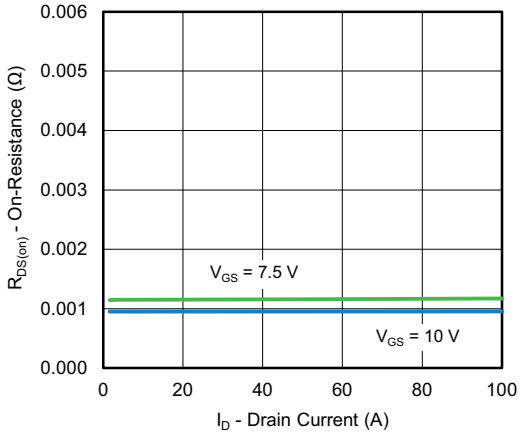
Transconductance



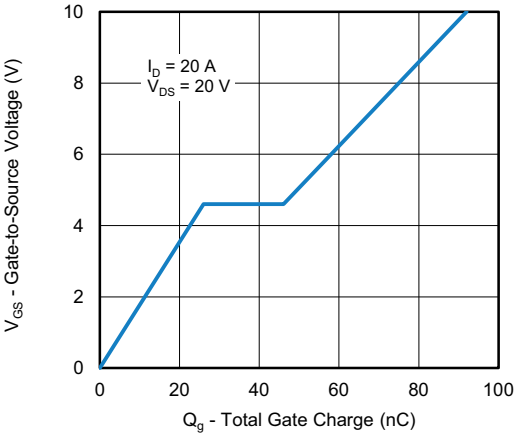
Transfer Characteristics



Capacitance

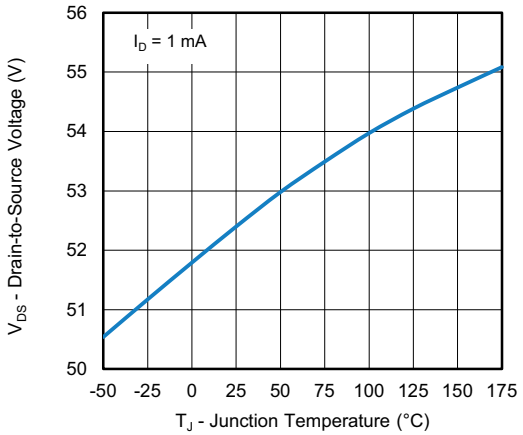


On-Resistance vs. Drain Current

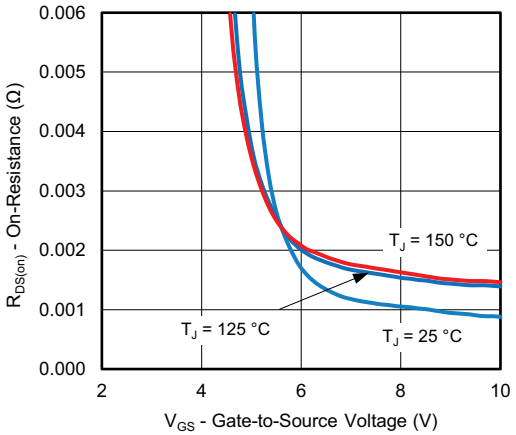


Gate Charge

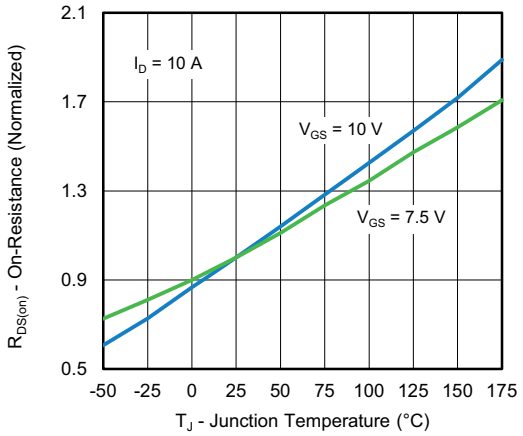
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



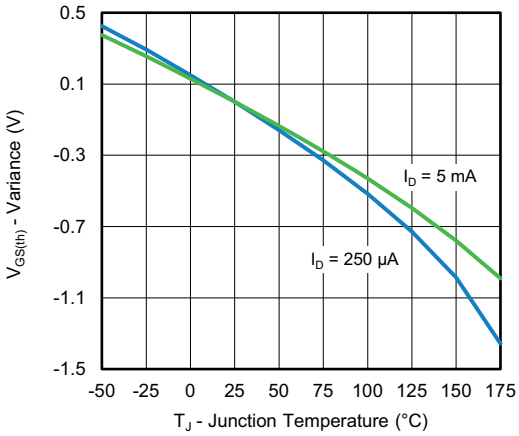
Drain Source Breakdown vs. Junction Temperature



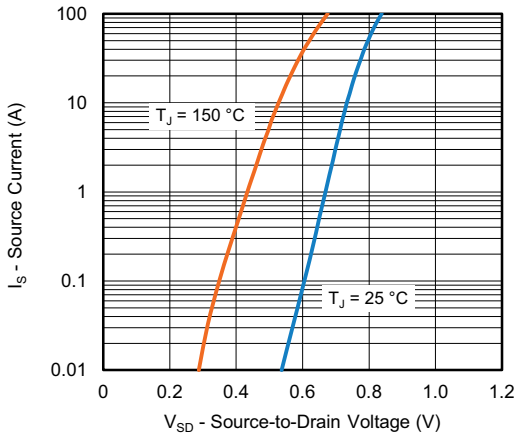
On-Resistance vs. Gate-to-Source Voltage



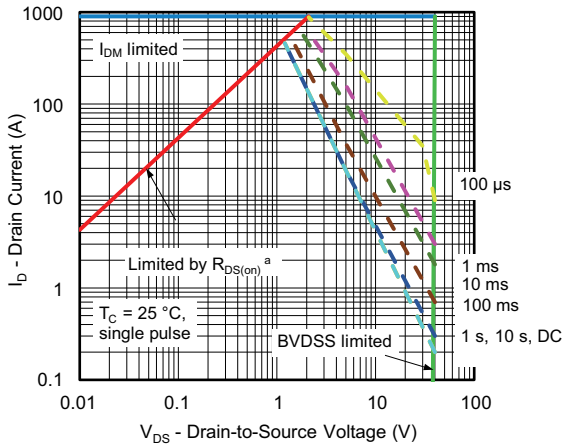
On-Resistance vs. Junction Temperature



Threshold Voltage



Source Drain Diode Forward Voltage

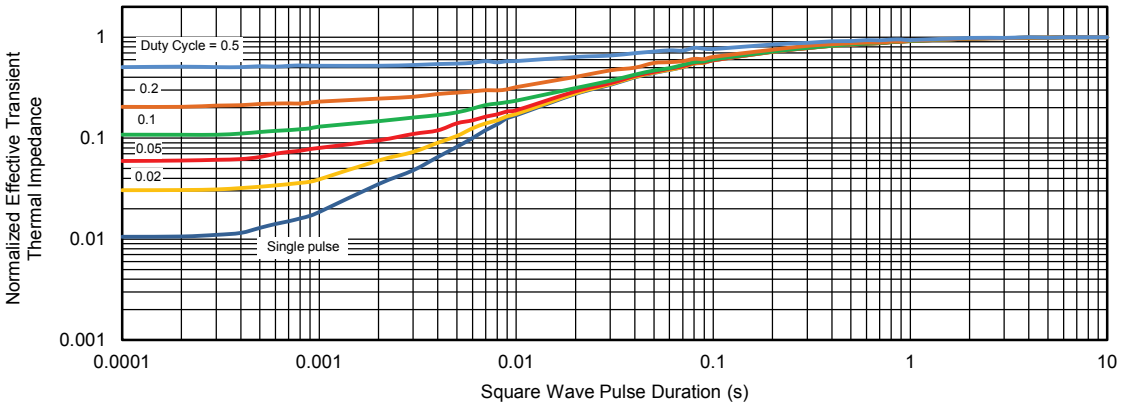


Safe Operating Area

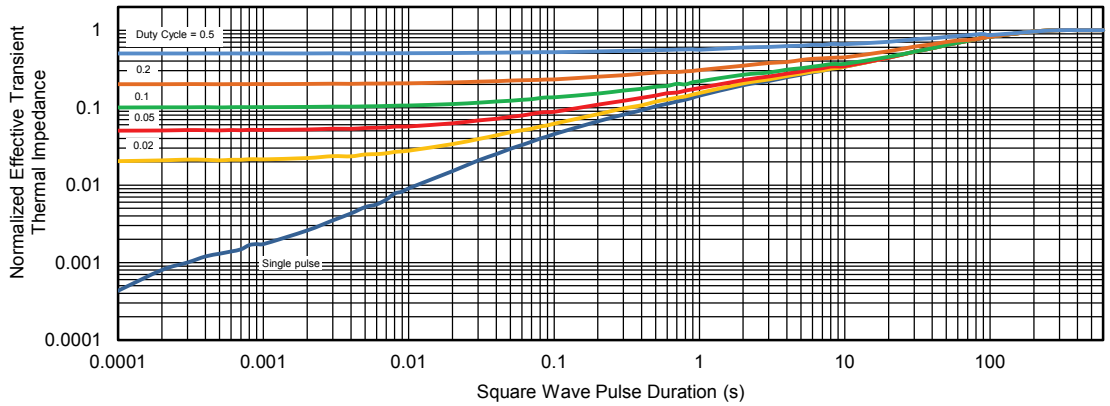
Note

a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?77320.

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, “Vishay”), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay’s knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer’s responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer’s technical experts. Product specifications do not expand or otherwise modify Vishay’s terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.